

Description

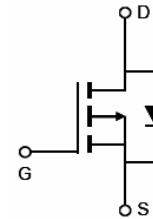
The NCE30P28Q uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or power management.

General Features

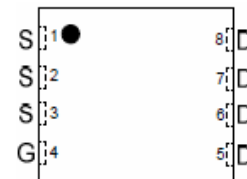
- $V_{DS} = -30V, I_D = -28A$
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 17m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Power management
- Load switch



Schematic diagram



Pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30P28Q	LCE30P28Q	DFN3.3X3.3-8			

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-28	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-80	A
Maximum Power Dissipation	P_D	40	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3.13	$^\circ C/W$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.8	-1.3	-2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-20A$	-	9.9	12	m Ω
	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-20A$	-	13.4	17	
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-20A$	-	25	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	2060	-	PF
Output Capacitance	C_{oss}		-	370	-	PF
Reverse Transfer Capacitance	C_{rss}		-	295	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-20A,$ $V_{GS}=-10V, R_{GEN}=3\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	9.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	24	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-20A, V_{GS}=-10V$	-	30	-	nC
Gate-Source Charge	Q_{gs}		-	4.5	-	nC
Gate-Drain Charge	Q_{gd}		-	9.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-28A$	-	-	-1.2	V

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

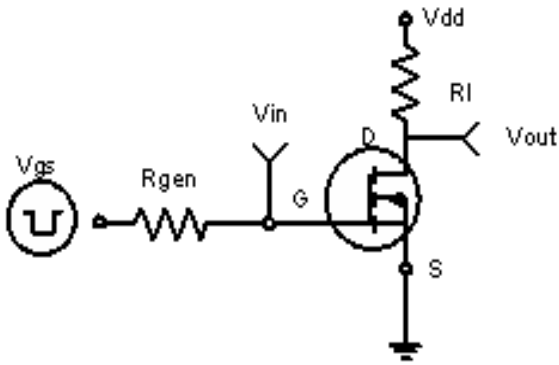


Figure 1 Switching Test Circuit

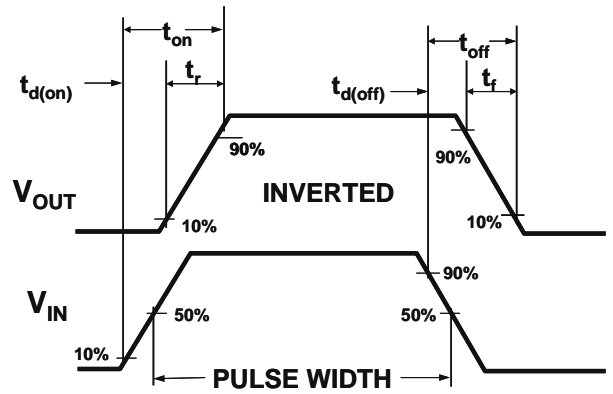


Figure 2 Switching Waveforms

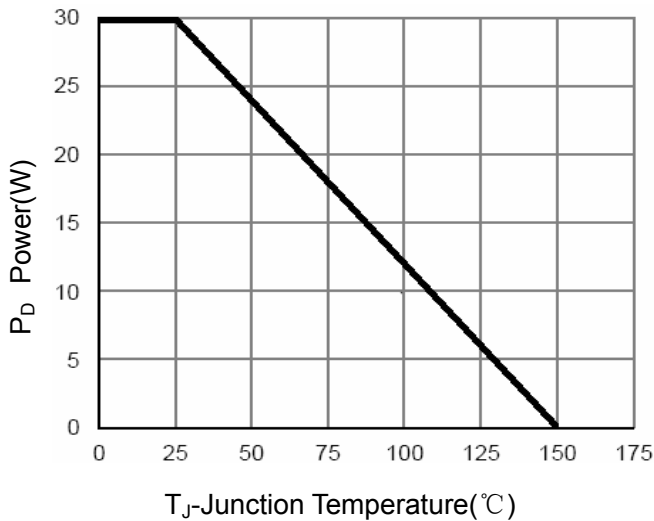


Figure 3 Power Dissipation

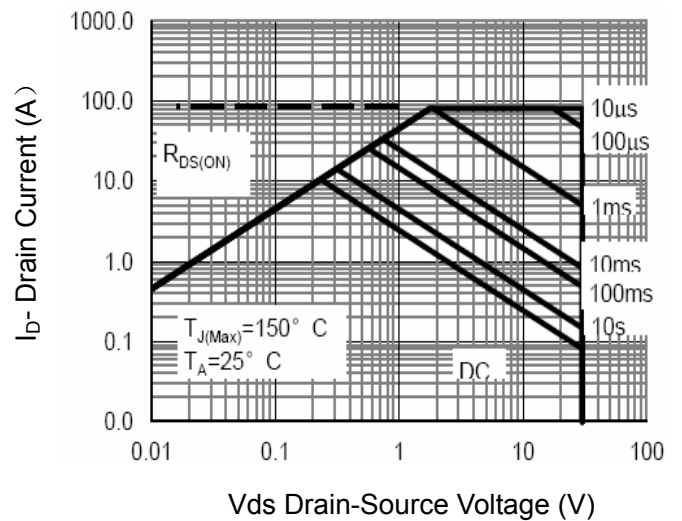


Figure 4 Safe Operation Area

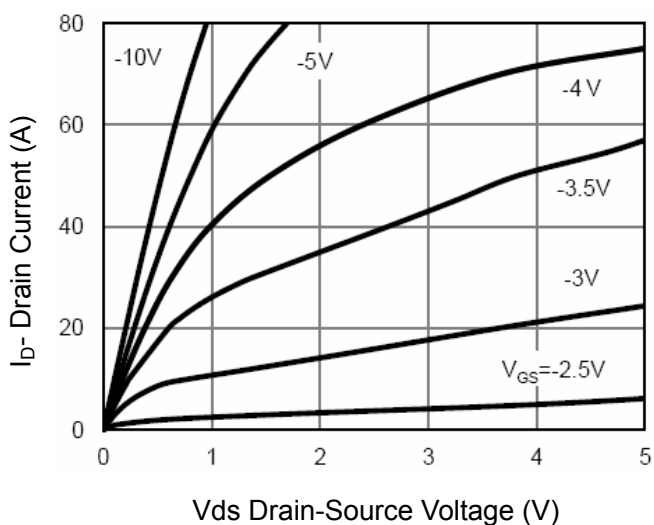


Figure 5 Output Characteristics

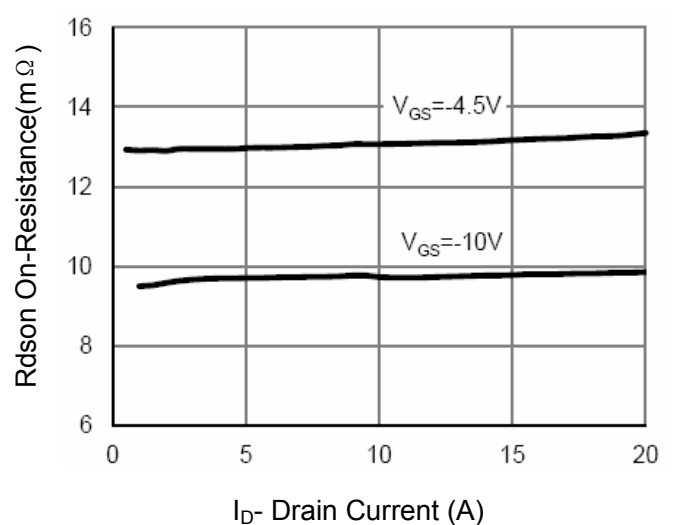


Figure 6 Drain-Source On-Resistance

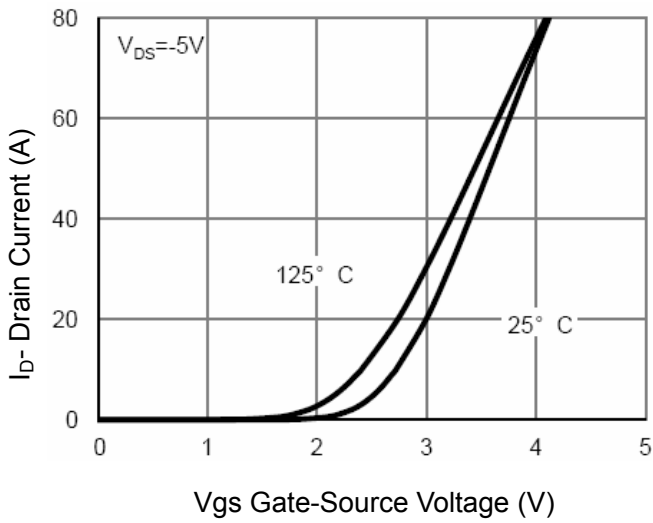


Figure 7 Transfer Characteristics

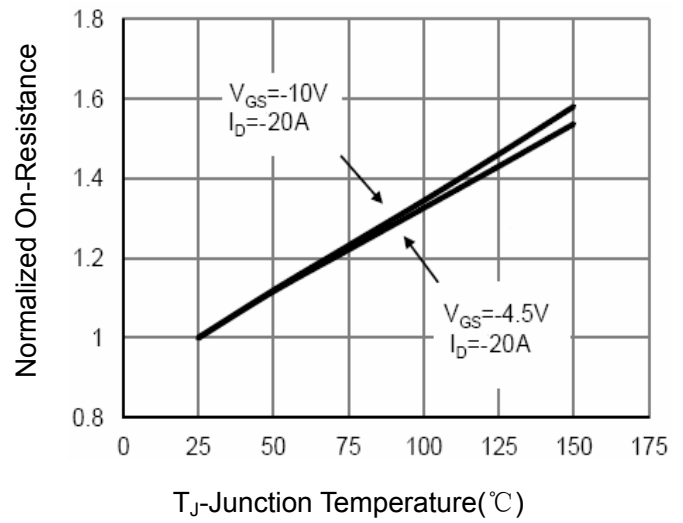


Figure 8 Drain-Source On-Resistance

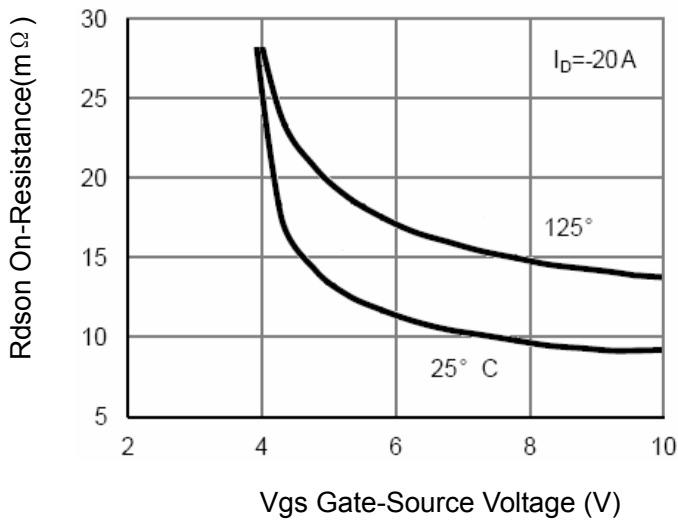


Figure 9 Rdson vs Vgs

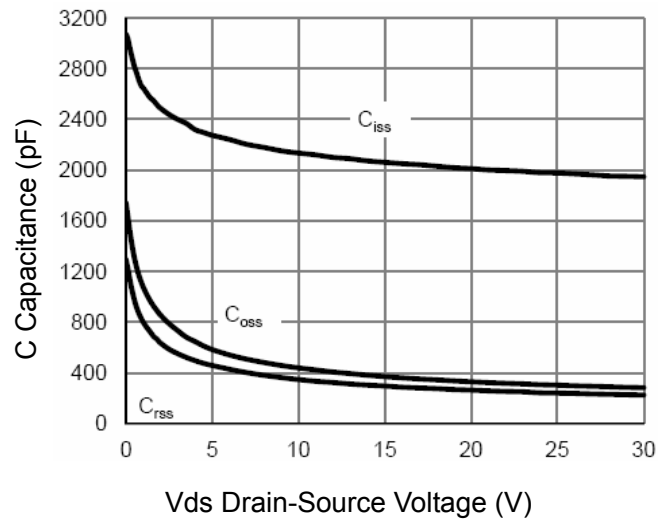


Figure 10 Capacitance vs Vds

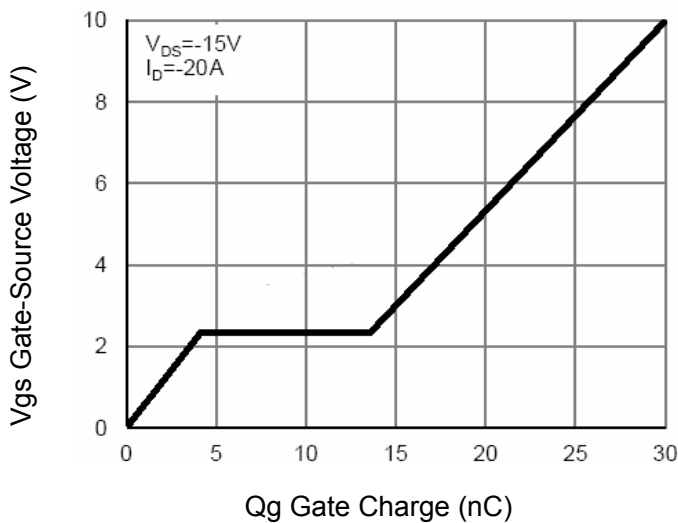


Figure 11 Gate Charge

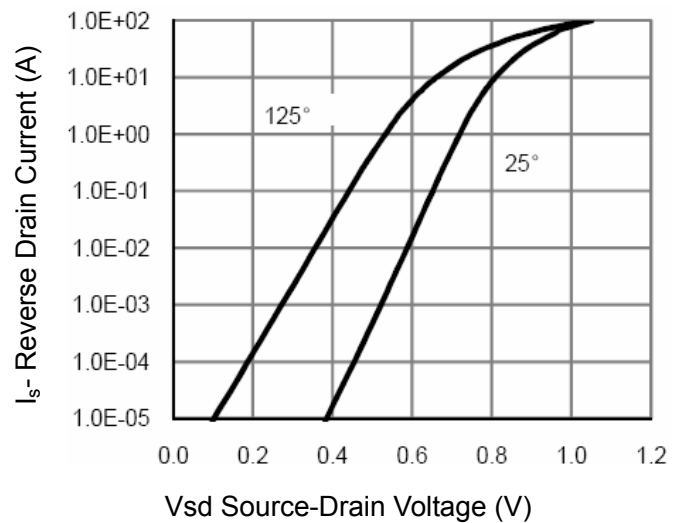


Figure 12 Source- Drain Diode Forward

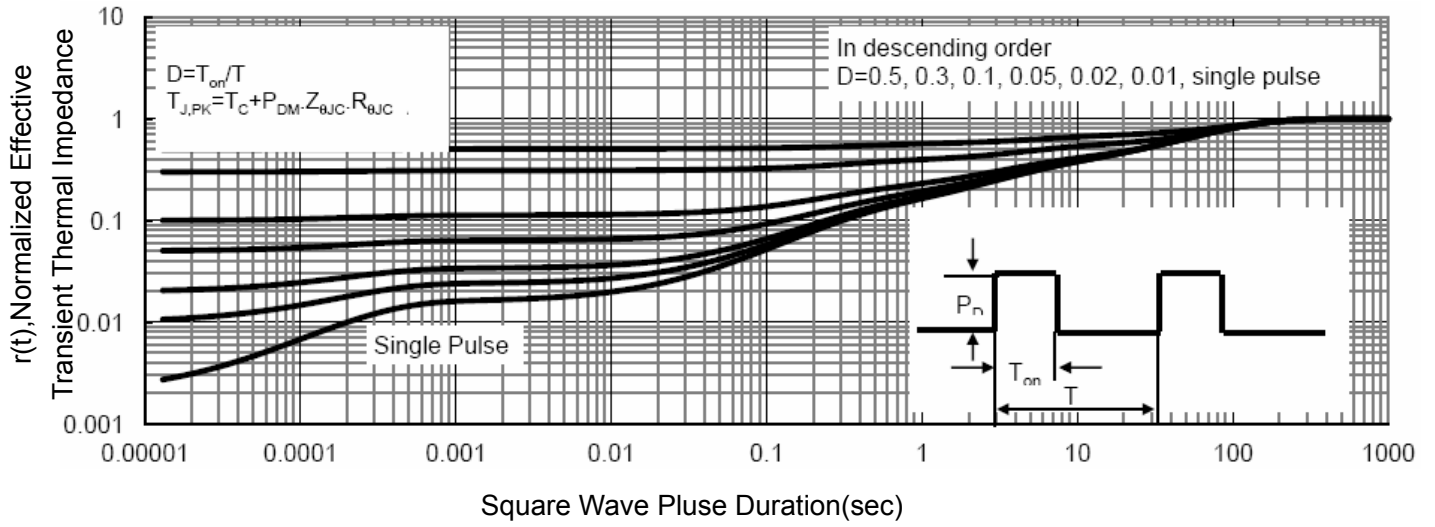
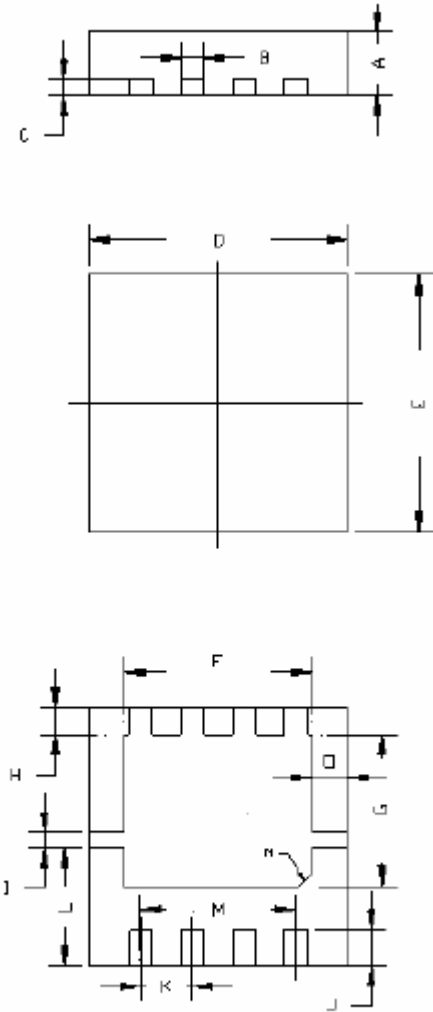


Figure 13 Normalized Maximum Transient Thermal Impedance

DFN3.3X3.3-8 Package Information

封装外形尺寸图				
	符号	单位: mm		
		MIN	MAX	TYP
	A	0.75	0.85	0.8
	B	0.25	0.35	0.3
	C	0.18	0.22	0.2
	D	3.2	3.3	3.25
	E	3.2	3.3	3.25
	F	2.2	2.5	2.35
	G	1.8	2.0	1.9
	H	0.3	0.4	0.35
	I	0.15	0.25	0.2
	J	0.4	0.5	0.45
	K	0.6	0.7	0.65
	L	1.38	1.58	1.48
	M	1.8	2.1	1.95
	N	0.15*45°		
	O	0.4	0.5	0.45